

Amendments to the Specification

Please substitute the following amended paragraph for the original paragraph that begins on page 3 at line 27.

Referring to Fig. 1, semiconductor device 10 represents generally an integrated circuit device such as a random access memory (RAM), a read only memory (ROM), or a logic circuit. The integrated circuits (not shown) are formed in a main region 12 of semiconductor device 10. The integrated circuits are electrically connected to wires 14 formed on an insulating layer 16. Insulating layer 16, typically made of phosphosilicate glass, is formed over the integrated circuits and usually extends to cover the entire upper surface of the device. Insulating layer 16 is patterned to open contact vias (not shown) to the integrated circuits in the main region 12 of semiconductor device 10. A metal layer formed over insulating layer 16 is patterned to form the wires 14. Passivation layer 18 is then formed over the entire surface of the device. Passivation layer 18 is patterned to expose select areas of the wires 14. These exposed areas constitute bond pads 20.